

Application Data Sheet

Application Information

Application Type::	Regular
Subject Matter::	Utility
Suggested classification::	
Suggested Group Art Unit::	
CD-ROM or CD-R?::	None
Computer Readable Form (CRF)?::	No
Title::	SEMICONDUCTOR DEVICE INCLUDING MOS FIELD EFFECT TRANSISTOR HAVING OFFSET SPACERS OR GATE SIDEWALL FILMS ON EITHER SIDE OF GATE ELECTRODE AND METHOD OF MANUFACTURING THE SAME
Attorney Docket Number::	016907-1577
Request for Early Publication?::	No
Request for Non-Publication?::	No
Suggested Drawing Figure::	
Total Drawing Sheets::	6
Small Entity?::	No
Petition included?::	No
Secrecy Order in Parent Appl.?::	No

Applicant Information

Applicant Authority Type::	Inventor
Primary Citizenship Country::	Japan
Status::	Full Capacity
Given Name::	Hitoshi
Family Name::	TSUNO

City of Residence:: Yokohama-shi
Country of Residence:: Japan
Street of mailing address:: c/o TOSHIBA CORPORATION
Intellectual Property Division
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Country of mailing address:: Japan

Correspondence Information

Correspondence Customer Number:: 22428
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Representative Information

Representative Customer Number::	22428	
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Domestic Priority Information

Application::	Continuity Type::	Parent Application::	Parent Filing Date::

Foreign Priority Information

Country::	Application number::	Filing Date::	Priority Claimed::
Japan	2003-091972	03/28/2003	Yes

Assignee Information

Assignee name:: KABUSHIKI KAISHA TOSHIBA